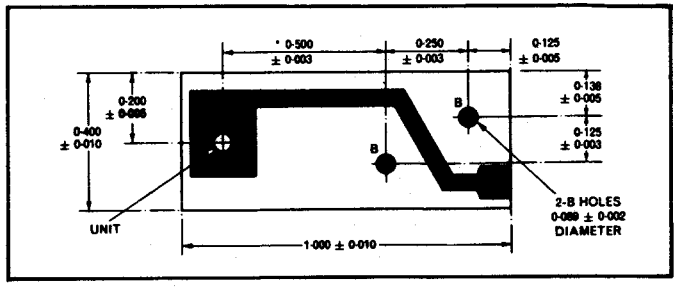
SDA 20

Ready-mounted cards containing LS600 Silicon sensor and the spectrally matched Gallium Arsenide Source Type TIL23

Parameter & Test Conditions	Id max. leakage current VCE(sensor) = 30V H = 0 IF(emitter) = 0 nA	VF max. static forward voltage IF(emitter) = 50mA V	Vce(sat) max. collector emitter saturation voltage IF(emitter) = 35mA IL = 200vA V	IL = 2mA V	I min. output current Vce(sensor) = 5V IF(emitter) = 35mA mA	Board Symbolisation
SDA20	100	1.5	—	—	0.10	/0
SDA20/1	100	1.5	0.5*	—	0.7	/1
SDA20/2	100	1.5	—	0.5†	2.0	/2

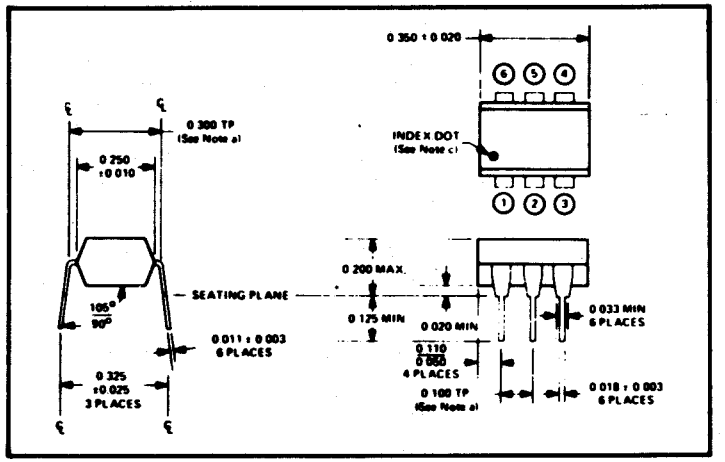
* This condition guarantees compatibility with low power TTL.
† This condition guarantees compatibility with normal power TTL



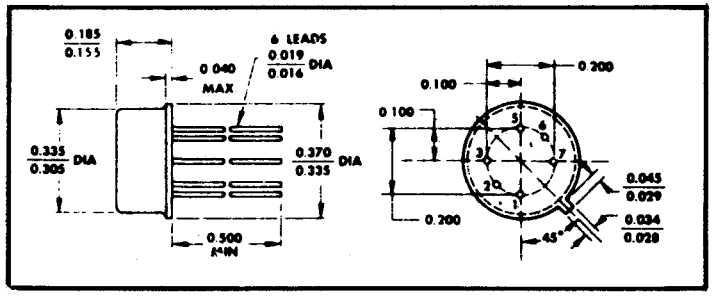
SDA20 Package

P—Dip Couplers

Device Type	Current Transfer Ratio Minimum %	at IF mA	Electrical Isolation Ratings kV	Package	Key Features
TIL111	12.5	16	1.5	A	Base lead provided for conventional transistor biasing. Six-pin dual-in-line plastic package
TIL112	2	10	1.5	A	
TIL113	300	10	1.5	A	
TIL114	12.5	16	2.5	A	
TIL115	2	10	2.5	A	
TIL116	20	10	2.5	A	
TIL117	50	10	2.5	A	
TIL118	6	10	1.5	A	
TIL119	300	10	1.5	A	
TIL124	10	10	5.0	A	Base lead provided for conventional transistor biasing. Six-pin dual-in-line plastic package
TIL125	20	10	5.0	A	
TIL126	50	10	5.0	A	
TIL127	300	10	5.0	A	
TIL128	300	10	5.0	A	



Device Type	Current Transfer Ratio Minimum %	at IF mA	Electrical Isolation Ratings kV	Package	Key Features
4N22*	25	10	1.0	B	JEDEC Version of TIL102
4N23*	60	10	1.0	B	JEDEC Version of TIL102A
4N24*	100	10	1.0	B	JEDEC Version of TIL103
TIL102	25	10	1.0	B	Hermetically sealed, Hi-Rel Coupler
TIL103†	100	10	1.0	B	High Gain Phototransistor Output
4N47	100	1	1.0	B	High Gain Phototransistor Output
4N48	200	1	1.0	B	
4N49	400	1	1.0	B	



* JAN versions available. † UK Defence Standard available.